

EAST - [10612842.wsp.1]

File View Edit Tools Window Help

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Active
 L1: (1) tunnel near magneto near resistance and through near hole and interconnection
 L2: (9) tunnel near magneto near resistance and through near hole
 L3: (31) tunnel near magneto near resistance and (through near hole hole)
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DBs US-PGF Plurals

Default operator OR light all hit terms initially

tunnel near magneto near resistance and (through near hole hole)

BRS form IS&R form Image Text

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	*
13	<input type="checkbox"/>	<input type="checkbox"/>	US 20020093845 A1	20020718	35	Magnetic semiconductor memory apparatus and method of manufacturing	365/97		
14	<input type="checkbox"/>	<input type="checkbox"/>	US 20020057594 A1	20020516	44	Magnetic memory and information recording and reproducing method therefor	365/171		
15	<input type="checkbox"/>	<input type="checkbox"/>	US 20020042158 A1	20020411	11	Method of fabricating a micro-technical structure, and micro-technical component	438/29	257/E27.005	
16	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039308 A1	20020404	6	MRAM configuration	365/158		
17	<input type="checkbox"/>	<input type="checkbox"/>	US 20010021124 A1	20010913	23	Magneto-resistive device and magneto-resistive effect type storage	365/158		
18	<input type="checkbox"/>	<input type="checkbox"/>	US 20010005301 A1	20010628	19	Spin tunnel magneto-resistance effect type magnetic sensor and production method	360/324.2	360/55	
19	<input type="checkbox"/>	<input type="checkbox"/>	US 6795339 B2	20040921	29	Thin film magnetic memory device having communication function, and distribution	365/171	365/173; 365/48;	
20	<input type="checkbox"/>	<input type="checkbox"/>	US 6724651 B2	20040420	39	Nonvolatile solid-state memory and method of driving the same	365/158	365/171; 365/173	
21	<input type="checkbox"/>	<input type="checkbox"/>	US 6587370 B2	20030701	44	Magnetic memory and information recording and reproducing method therefor	365/171	365/158; 365/173;	
22	<input type="checkbox"/>	<input type="checkbox"/>	US 6587318 B2	20030701	19	Spin tunnel magneto-resistance effect type magnetic sensor and production method	360/324.2		
23	<input type="checkbox"/>	<input type="checkbox"/>	US 6560135 B2	20030506	34	Magnetic semiconductor memory apparatus and method of manufacturing	365/97	365/171; 365/173	